

<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>				Docket Number		Application Number	
				M4065.0210/P210-A		Not Yet Assigned	
				Applicant(s)			
				Dan Gealy et al.			
Filing Date				Group Art Unit			
December 5, 2001				2814			
<b>U.S. PATENT DOCUMENTS</b>							
*EXAMINER INITIAL	REF	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
WZ		5142438	08/14/92	Reimberg et al.	361	313	
<b>FOREIGN PATENT DOCUMENTS</b>							
	REF	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translations YES NO
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
WZ	A	G. W. Dietz et al., "LEAKAGE CURRENTS IN $\text{Ba}_{0.7}\text{Sr}_{0.3}\text{TiO}_3$ THIN FILMS FOR ULTRAHIGH-DENSITY DYNAMIC RANDOM ACCESS MEMORIES," J. Appl. Phys. 82 (5), September 1, 1997, American Institute of Physics, pages 2359-2364.*					
	B	Tomonori Aoyama et al., "ULTRATHIN $\text{Ta}_2\text{O}_5$ FILM CAPACITOR WITH Ru BOTTOM ELECTRODE," J. Electrochem. Soc. Vol. 145, No. 8, August 1998, The Electrochemical Society, Inc., pages 2961-2963.*					
	C	Benjamin Chih-ming Lai et al., "LEAKAGE CURRENT MECHANISM OF METAL- $\text{Ta}_2\text{O}_5$ METAL CAPACITORS FOR MEMORY DEVICE APPLICATION," Journal of the Electrical Society, 146 (1) pages 266-269 (1999).*					

EXAMINER	DATE CONSIDERED
Not Yet Assigned	12/23/02
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.	